a first conducting film formed over the base substrate and including two conductor patterns adjacent to each other;

an etching stopper film covering an each upper surface of the two conductor patterns;

a first insulation film formed over the etching stopper film and the base substrate;

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a contract hole, located between the two conductor patterns, reaching the base substrate through the first insulation film, wherein an end of the contact hole is positioned on the etching stopper film; and

a sidewall insulation film formed on an inner wall of the first insulation film, each side wall of the two conductor patterns, and each side wall of the etching stopper film in the contact hole,

wherein each of said etching stopper films is completely covered by said first insulation film and said respective sidewall insulation film.

2. (Twice Amended) A semiconductor device comprising:

a base substrate;

a first conducting film formed over the base substrate and including a plurality of conductor patterns adjacent to each other;

an etching stopper film covering an upper surface of the conducting patterns;

a first insulation film [selectively buried] which is filling spaces between said [a] plurality of conductor patterns and not extending over the etching stopper film; [and includes]

a contact hole located between the adjacent conductor patterns and having an end thereof defined by the conductor patterns; and

a sidewall insulation film formed on an inner wall of the contact hole so that side walls of the conductor pattern and the etching stopper film are covered.

9. (Twice Amended) A semiconductor device comprising;

a semiconductor substrate;

a plurality of word lines formed over the semiconductor substrate and extended in a first direction;

an etching stopper film covering upper surfaces of the word lines;

a first insulation film formed over the etching stopper film and the semiconductor substrate;

a contact hole, located between the word lines, reaching the semiconductor substrate through the first insulation film, wherein an end of the contact hole is positioned on the etching stopper film; and

a sidewall insulation film, formed in the contact hole, covering a side wall of the first insulation film, side walls of the word lines and side walls of the etching stopper film,

the contact hole having a first width which is larger than a space between the adjacent word lines at a top of the contact hole and a second width which is substantially the same as a width subtracted twice a width of the sidewall insulation film from the space between the adjacent word lines at a bottom of the contact hole.

11. (Twice Amended) A semiconductor device comprising:

a semiconductor substrate;

a plurality of word lines formed over the semiconductor substrate and extended in a first direction;

a first insulation film formed over the word lines and the semiconductor substrate;

a plurality of bit lines formed over the first insulation film and extended in a second direction which intersects the first direction;

an etching stopper film covering upper surfaces of the bit lines;

a second insulation film formed over the etching stopper film and the first insulation film;

a contact hole, located between the adjacent bit lines, having an end thereof positioned on the etching stopper film;

a sidewall insulation film, formed in the contact hole, covering a side wall of the second insulation film, side walls of the bit lines and side walls of the etching stopper film; and

a capacitor having one electrode connected to the semiconductor substrate through the contact hole,

the contact hole having a first width which is larger than a space between the adjacent bit lines at a top of the contact hole and a second with which is substantially the same as a width subtracted twice a width of the sidewall insulation film from the space between the adjacent bit lines at a bottom of the contact hole.

12. (Twice Amended) A semiconductor device comprising:

a semiconductor substrate;

a plurality of word lines formed over the semiconductor substrate and extended in a first direction;

a first insulation film formed over the word lines and the semiconductor substrate;

a plurality of bit lines formed over the first insulation first and extended in a second direction which intersects the first direction;

an etching stopper film covering upper surfaces of the bit lines;

a second insulation film [selectively buried] which is filling spaces between said [a] plurality of bit lines and not extending over the etching stopper film;

a contact hole, located between the adjacent bit lines, having an end thereof defined by the bit lines;

a sidewall insulation film, formed in the contact hole, covering a side wall of the second insulation film, side walls of the bit lines and side walls of the etching stopper film; and

a capacitor having one electrode connected to the semiconductor substrate through the contact hole.

36. (Amended) A semiconductor device [according to claim 1, wherein] comprising:

a base substrate;

a first conducting film formed over the base substrate and including patterns adjacent to each other;

an etching stopper film covering each upper surface of the two conductor patterns;

a first insulation film formed over the etching stopper film and the base substrate;

a contact hole, located between the two conductor patterns, reaching the base substrate through the first insulation film, wherein an end of the contract hole is positioned on the etching stopper film; and

a sidewall insulation film formed on an inner wall of the first insulation film, each side wall is of the two conductor patterns, and each side wall of the etching stopper film in the contact hole, in which

the end of the contact hole is defined by four sides including a first pair of sides which are opposed to each other and a second pair of sides which are opposed to each other,

the first pair of sides is defined by the conductor patterns, and

the second pair of sides is defined by the first insulation film.

Please add new claim 37 as follows:

--37. A semiconductor device comprising:

a base substrate;

a first conducting film formed over the base substrate and including two conductor patterns adjacent to each other;

an etching stopper film covering each upper surface of the two conductor patterns;

a first insulation film formed over the etching stopper film and the base substrate;